

ABSTRACT

A sensing circuit comprises a charge integrating sense amplifier 4 serially coupled to a discriminator 6. The sensing circuit can be used to sense the logic status of the cells in a random access memory (RAM) system, including ferroelectric RAMs. The use of a charge integrating sense amplifier enables the effect of bit line capacitance intrinsic to RAM circuits to be overcome and also provides efficient charge to voltage conversion gain.

Figure 3